Stacking-Fault Formation and Propagation in 4H-SiC PiN Diodes*

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During the production process, some information was omitted from Figs. 1 and 4 for this paper. Corrected versions of these figures appear below.

Fig. 1. Comparison of (a) forward-voltage degradation and (b) stacking-fault growth. The stressing current 1 A (160 A/cm^2) was reduced to 0.5 A (80 A/cm^2) during the two intervals shaded gray. The image pairs shown in Fig. 2 were taken at $t = 0 \text{ min}$, 2.4 min, 22 min, and 44 min. Arrows show the last three times.

Fig. 4. Growth of stacking faults. The stressing current was 1 A (160 A/cm^2) except during the two intervals indicated in gray, when it was reduced to 0.5 A (80 A/cm^2). The distance of the lower tip of the stacking fault from the top of the diode anode, as indicated in the inset, is plotted.

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